



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SOT89 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

BF621

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FEATURES

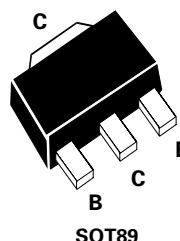
- * High breakdown and low saturation voltage

APPLICATIONS

- * Suitable for video output stages in TV sets
- * Switching power supplies

COMPLEMENTARY TYPE – BF620

PARTMARKING DETAIL – DF



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-100	mA
Continuous Collector Current	I_C	-50	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	-1	W
Operating and Storage Temperature Range	$T_j:T_{stg}$	-65 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300		V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300		V	$I_C = -1mA, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -100\mu A, I_C = 0$
Collector Cut-Off Current	I_{CBO}		-10 -20	nA μA	$V_{CB} = -200V, I_E = 0$ $V_{CB} = -200V, I_E = 0 \uparrow$
Collector Cut-Off Current	I_{CER}		-50 -10	nA μA	$V_{CE} = -200V, R_{BE} = 2.7K\Omega$ $V_{CE} = -200V, R_{BE} = 2.7K\Omega \uparrow$
Emitter Cut-Off Current	I_{EBO}		-10	μA	$V_{EB} = -5V, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.6	V	$I_C = -30mA, I_B = -5mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	V	$I_C = -20mA, I_B = -2mA^*$
Static Forward Current Transfer Ratio	h_{FE}	50			$I_C = -25mA, V_{CE} = -20V^*$
Transition Frequency	f_T		100 Typical	MHz	$I_C = -10mA, V_{CE} = -10V$ $f = 100MHz$
Output Capacitance	C_{obo}		0.8 Typical	pF	$V_{CB} = -30V, f = 1MHz$

$\uparrow T_{amb} = 150^{\circ}C$

*Measured under pulsed conditions.

For typical characteristics graphs see FMMTA92 datasheet.

